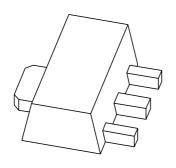
### **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# BSR40; BSR41; BSR42; BSR43 NPN medium power transistors

Product data sheet Supersedes data of 1999 Apr 28 2004 Dec 13



## NPN medium power transistors

BSR40; BSR41; BSR42; BSR43

### **FEATURES**

- High current (max. 1 A)
- Low voltage (max. 80 V).

### **APPLICATIONS**

- Thick and thin-film circuits
- Telephony and general industrial applications.

### **DESCRIPTION**

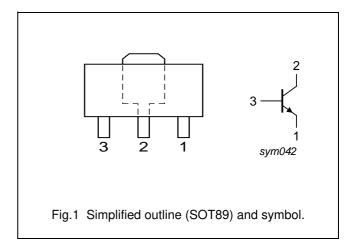
NPN medium power transistor in a SOT89 plastic package. PNP complements: BSR30; BSR31 and BSR33.

### **MARKING**

TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE	
BSR40	AR1	BSR42	AR3	
BSR41	AR2	BSR43	AR4	

### **PINNING**

PIN	DESCRIPTION	
1	emitter	
2	collector	
3	base	



### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE				
TIPE NOMBER	NAME	DESCRIPTION	VERSION			
BSR40	SC-62	plastic surface mounted package; collector pad for good heat	SOT89			
BSR41		transfer; 3 leads				
BSR42						
BSR43						

### NPN medium power transistors

BSR40; BSR41; BSR42;

**BSR43** 

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BSR40; BSR41		_	70	V
	BSR42; BSR43		_	90	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BSR40; BSR41		_	60	V
	BSR42; BSR43		_	80	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V
I <sub>C</sub>	collector current (DC)		_	1	Α
I <sub>CM</sub>	peak collector current		_	2	Α
I <sub>BM</sub>	peak base current		_	0.2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	-	1.35	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C

### Note

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	93	K/W
R <sub>th(j-s)</sub>	thermal resistance from junction to soldering point		13	K/W

### Note

<sup>1.</sup> Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. For other mounting conditions, see "Thermal considerations for SOT89 in the General Part of associated Handbook".

<sup>1.</sup> Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. For other mounting conditions, see "Thermal considerations for SOT89 in the General Part of associated Handbook".

# NPN medium power transistors

BSR40; BSR41; BSR42; BSR43

### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	I <sub>E</sub> = 0 A; V <sub>CB</sub> = 60 V	_	100	nA
		I <sub>E</sub> = 0 A; V <sub>CB</sub> = 60 V; T <sub>j</sub> = 150 °C	_	50	μА
I <sub>EBO</sub>	emitter-base cut-off current	I <sub>C</sub> = 0 A; V <sub>EB</sub> = 5 V	_	100	nA
h <sub>FE</sub>	DC current gain	$I_C = 100 \mu A; V_{CE} = 5 V; note 1$			
	BSR40; BSR42		10	_	
	BSR41; BSR43		30	_	
	DC current gain	I <sub>C</sub> = 100 mA; V <sub>CE</sub> = 5 V; note 1			
	BSR40; BSR42		40	120	
	BSR41; BSR43		100	300	
	DC current gain	I <sub>C</sub> = 500 mA; V <sub>CE</sub> = 5 V; note 1			
	BSR40; BSR42		30	_	
	BSR41; BSR43		50	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 150 mA; I <sub>B</sub> = 15 mA; note 1	_	250	mV
		$I_C = 500 \text{ mA}$ ; $I_B = 50 \text{ mA}$ ; note 1	_	500	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 150 mA; I <sub>B</sub> = 15 mA; note 1	_	1	V
		$I_C = 500 \text{ mA}$ ; $I_B = 50 \text{ mA}$ ; note 1	_	1.2	V
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = i <sub>e</sub> = 0 A; V <sub>CB</sub> = 10 V; f = 1 MHz	_	12	pF
C <sub>e</sub>	emitter capacitance	$I_C = I_c = 0 \text{ A}; V_{EB} = 0.5 \text{ V}; f = 1 \text{ MHz}$	_	90	pF
f <sub>T</sub>	transition frequency	$I_C = 50 \text{ mA}; V_{CE} = 10 \text{ V}; f = 100 \text{ MHz}$	100	_	MHz
Switching	times (between 10% and 90% levels	s)	•	•	•
t <sub>on</sub>	turn-on time	I <sub>Con</sub> = 100 mA; I <sub>Bon</sub> = 5 mA;	_	250	ns
t <sub>off</sub>	turn-off time	$I_{Boff} = -5 \text{ mA}$	_	1	μS

### Note

1. Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.01.$ 

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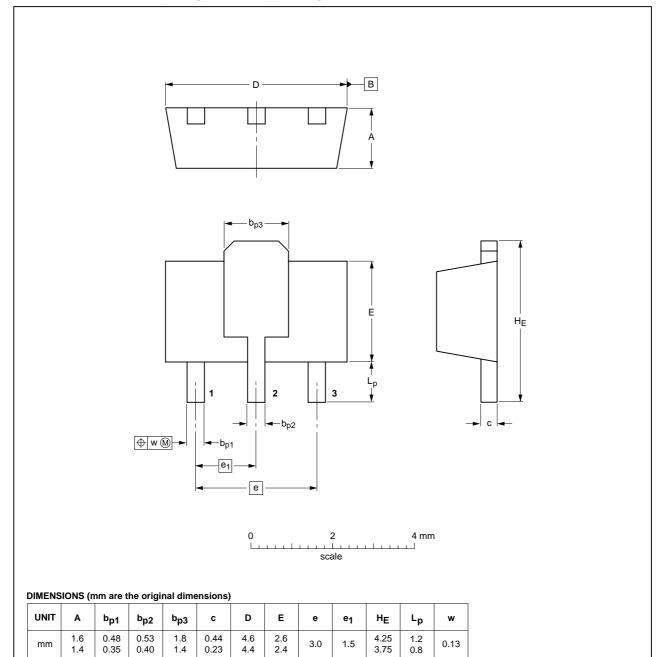
## NPN medium power transistors

BSR40; BSR41; BSR42; BSR43

### **PACKAGE OUTLINE**

### Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



OUTLINE	REFERENCES			EUROPEAN	ICCUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION ISSUE DATE	
SOT89		TO-243	SC-62			<del>-04-08-03</del> 06-03-16

### NPN medium power transistors

BSR40; BSR41; BSR42; BSR43

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

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### **Contact information**

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